

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original): A method for manufacturing a semiconductor integrated device, comprising:

a first step of forming an integrated circuit element in each region on a semiconductor substrate partitioned by a scribe line;

a second step of forming internal wiring extending toward a boundary of adjacent integrated circuit elements;

a third step of forming a groove along the scribe line on a back surface of the semiconductor substrate to expose a portion of the internal wiring;

a fourth step of forming a metal film covering the back surface of the semiconductor substrate and the groove;

a fifth step of patterning the metal film to form external wiring and removing the metal film at a bottom portion of the groove;

a sixth step of forming a protection film covering the external wiring and the bottom portion of the groove; and

a seventh step of separating the semiconductor substrate along the scribe line.

2. (original): A method for manufacturing a semiconductor integrated device according to Claim 1, wherein

in the seventh step, the semiconductor substrate is separated with a cutting width which is narrower than a width of the bottom portion of the groove.

3. (currently amended): A method for manufacturing a semiconductor integrated device according to Claim 1, wherein

in the fifth step, the metal film on the bottom portion of the groove is removed in a width wider than a cutting width in a separation of the ~~sixth~~ seventh step.

4. (original): A semiconductor integrated device comprising:

a semiconductor chip in which an integrated circuit element is formed on a semiconductor substrate;

internal wiring formed on the semiconductor substrate and extending to a side periphery of the semiconductor substrate; and

external wiring formed detouring around a side surface of the semiconductor chip and connected to the internal wiring, wherein

an end of the external wiring is covered by a protection film.

5. (original): A semiconductor integrated device according to Claim 4, wherein

the end of the external wiring is positioned internal to a side surface of the semiconductor integrated device.

6. (original): A semiconductor integrated device according to Claim 4, wherein

the external wiring is made of aluminum to which copper is added.

7. (original): A semiconductor integrated device according to Claim 4, wherein

the internal wiring is made of aluminum to which copper is added.